



Attorney Docket No. 5308-279

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Sei-Hyung Ryu

Serial No.: 10/698,170

Filed: October 30, 2003

For: *Vertical JFET Limited Silicon Carbide Power Metal-Oxide Semiconductor Field Effect Transistors And Methods Of Fabricating Vertical JFET Silicon Carbide Metal-Oxide Semiconductor Field Effect Transistors*

Date: February 18, 2004

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Group Art Unit: 2811

Confirmation No. 2502

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. § 1.97(b)

Sir:

Attached is a list of documents on Form PTO-1449, together with a copy of any listed foreign patent document and/or non-patent literature. A copy of any listed U.S. patent and/or U.S. patent application publication is not provided herewith in accordance with the waiver by the U.S. Patent and Trademark Office of requirements under 37 C.F.R. § 1.98(a)(2)(i) for all U.S. national patent applications filed after June 30, 2003 and for all international applications that have entered the national stage under 35 USC § 371 after June 30, 2003.

It is requested that these documents be considered by the Examiner and officially made of record in accordance with the provisions of 37 C.F.R. § 1.56 and Section 609 of the MPEP.

No fee is believed due. However, the Commissioner is hereby authorized to charge any deficiency or credit any overpayment to Deposit Account No. 50-0220.

Respectfully submitted,

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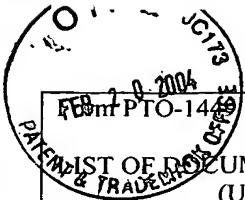
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CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents P.O. Box 1450, Alexandria, VA 22313-1450, on February 18, 2004.

Michele P. McMahan



U.S. Department of Commerce Patent and Trademark Office LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)					Attorney Docket No. 5308-279	Serial No. 10/698,170	
					Applicant: Sei-Hyung Ryu		
					Filing Date: October 30, 2003	GAU: 2811	
U.S. PATENT DOCUMENTS							
Examiner Initials		Document No.	Date (m/d/y)	Name	Class	Subclass	Filing Date if Appropriate
	1	6,610,366	8/26/03	Lipkin	427	378	4/12/01
	2	6,316,791	11/13/01	Schorner et al.	257	77	
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		Document Number	Date	Country	Class	Subclass	Translation (Yes/No)
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OTHER DOCUMENTS							
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	15	Baliga, Power Semiconductor Devices, Chapter 7, PWS Publishing, 1996					
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	17	United States Provisional Patent Application Serial No. 60/294,307					
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	21	Kobayashi et al. "Dielectric Breakdown and Current Conduction of Oxide/Nitride/Oxide Multi-Layer Structures," <i>1990 IEEE Symposium on VLSI Technology</i> . pp. 119-120.					
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	25	Dahlquist et al. "A 2.8kV, Forward Drop JBS Diode with Low Leakage," <i>Materials Science Forum</i> , Vols. 338-342, (2000) pp. 1179-82.					
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	27	Motorola Power MOSFET Transistor Databook, 4th edition. Motorola, Inc., 1989, pp. 2-5-4 - 2-5-7.					
	28	Ryu et al. Article and Presentation: "27 mΩ-cm ² , 1.6 kV Power DiMOSFETs in 4H-SiC," <i>Proceedings of the 14 International Symposium on Power Semiconductor Devices & ICs 2002</i> , June 4-7, 2002, Santa Fe, NM.					
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Examiner:

Date Considered:

Examiner:

Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.